L Number	Hits	Search Text	DB	Time stamp
-	49	((oxide adj film) near10 (apart or separate or separated or separation or separating or isolate or isolated) near10 surface near10 (semiconductor adj substrate)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:02
-	17	((oxide adj film) near10 (apart or separate or separated or separation or separating or isolate or isolated) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:05
-	3	((oxide adj film) near10 (apart or separate or separated or separation or separating or isolate or isolated) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)).clm. and (epitaxy or epitaxially or epitaxial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:06
-	22	((oxide adj film) near10 (apart or separate or separated or separation or separating or isolate or isolated) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)) and (epitaxy or epitaxially or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:07
-	3	((oxide adj film) near10 (apart) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)) and (epitaxy or epitaxially or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:12
-	27	((oxide adj film) near10 (apart or between) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)) and (epitaxy or epitaxially or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:15
-	5	((oxide adj film) near10 (apart or between) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)).clm. and (epitaxy or epitaxially or epitaxial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:20
-	5	((oxide adj film) near10 (apart or between or buried) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)).clm. and (epitaxy or epitaxially or epitaxial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:21

-		2	((oxide adj film) near10 (apart or between or buried) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)).clm. same (epitaxy or epitaxially or epitaxial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:21
-		5	((oxide adj film) near10 (apart or between or buried) near10 ((main or reverse or first or second or upper or lower or opposite) adj surface) near10 (semiconductor adj substrate)) same (epitaxy or epitaxially or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:23
-		84	((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same (epitaxy or epitaxially or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:24
-		6	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same (epitaxy or epitaxially or epitaxial)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:26
-		5	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:29
-		59	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:30
-		18	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31
-		15	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and (oxide near film).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31
-		15	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and (oxide adj film).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31

-	8	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and (oxide adj film).clm. and (oxide adj film).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:32
-	0	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and (oxide adj film).clm. and (oxide adj film).ab. and ((auto near doping) or warpage).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:33
-	2	(((oxide adj film) near10 (apart or between or buried) near10 (semiconductor adj substrate)) same ((epitaxy or epitaxially or epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and (oxide adj film).clm. and (oxide adj film).ab. and ((auto near doping) or warpage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:33